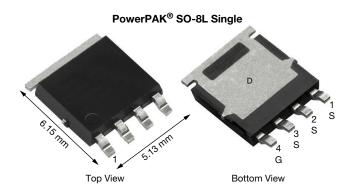


Vishay Siliconix

# Automotive N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V <sub>DS</sub> (V)	40
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0024
I <sub>D</sub> (A)	75
Configuration	Single

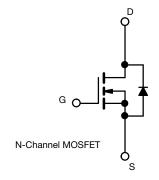
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJA76EP (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATINGS (To	c = 25 °C, unles	s otherwise noted	)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	40	V
Gate-source voltage		$V_{GS}$	± 20	V
Continuous drain current	T <sub>C</sub> = 25 °C <sup>a</sup>	1	75	
Continuous drain current	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	65.6	
Continuous source current (diode conduction)		I <sub>S</sub>	62	Α
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	200	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	44	
Single pulse avalanche energy	L = 0.1 IIII1	E <sub>AS</sub>	96.8	mJ
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	68	W
Maximum power dissipation -	T <sub>C</sub> = 125 °C	F <sub>D</sub>	22	VV
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Soldering recommendations (peak temperature) d, e			260	C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	$R_{thJA}$	68	°C/W
Junction-to-case (drain)		R <sub>thJC</sub>	2.2	G/VV

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



# Vishay Siliconix

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static	•				•	I.		
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = 250 \mu A$		40	-	-	V	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	· V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.5	3.0	3.5	V	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V	-	-	1		
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	200	1	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A	-	0.0020	0.0024	Ω	
Drain-source on-state resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C	-	-	0.0040		
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C	-	-	0.0050		
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		-	48	-	S	
Dynamic <sup>b</sup>								
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 25 V, f = 1 MHz	-	4005	5250	pF	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	1160	1550		
Reverse transfer capacitance	C <sub>rss</sub>			-	90	120		
Total gate charge <sup>c</sup>	Qg			-	66	100		
Gate-source charge c	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, I_D = 10 \text{ A}$	-	17	-	nC	
Gate-drain charge <sup>c</sup>	$Q_{gd}$			-	14	-		
Gate resistance	$R_g$		f = 1 MHz	0.35	0.76	1.2	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	17	30		
Rise time <sup>c</sup>	t <sub>r</sub>		= 20 V, $R_L = 2 \Omega$	-	17	30	no	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	32	50	ns	
Fall time <sup>c</sup>	t <sub>f</sub>				8	15		
Source-Drain Diode Ratings and Chara	cteristics <sup>b</sup>							
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	200	Α	
Forward voltage	$V_{SD}$	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V		-	0.76	1.2	V	
Body diode reverse recovery time	t <sub>rr</sub>			-	65	130	ns	
Body diode reverse recovery charge	Q <sub>rr</sub>	J 10	A, di/dt = 100 A/µs	1	123	250	nC	
Reverse recovery fall time	ta	] IF = 10	A, u/ul = 100 A/µS	-	35	-	ns	
Reverse recovery rise time	t <sub>b</sub>	]		-	30	-	ns	
Body diode peak reverse recovery	I <sub>RM(REC)</sub>			_	-3.3	_	Α	

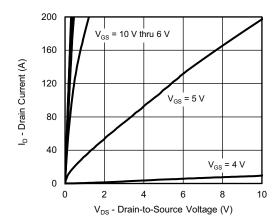
### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

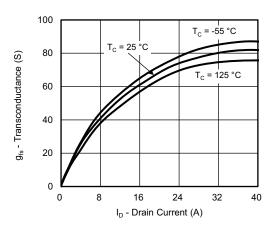
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



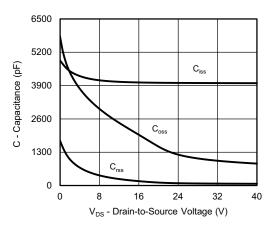
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



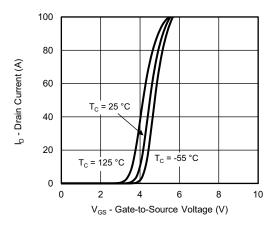
#### **Output Characteristics**



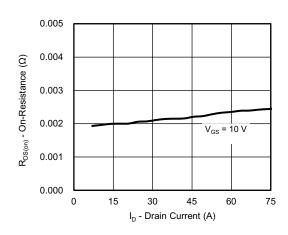
Transconductance



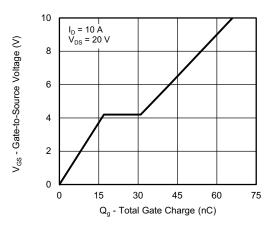
Capacitance



**Transfer Characteristics** 



On-Resistance vs. Drain Current

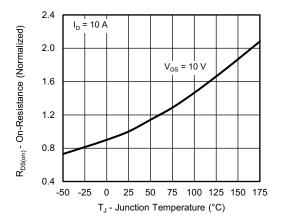


**Gate Charge** 

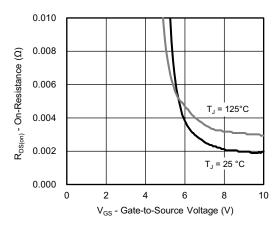
For technical questions, contact: automostechsu



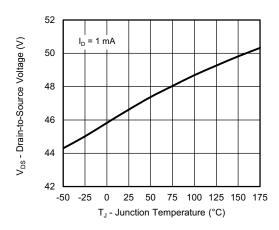
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



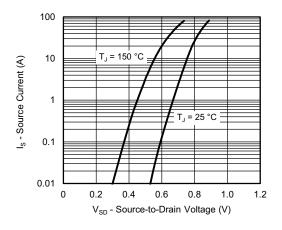
On-Resistance vs. Junction Temperature



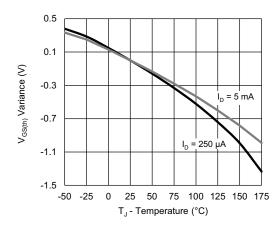
On-Resistance vs. Gate-to Source Voltage



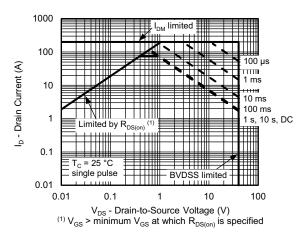
**Drain Source Breakdown vs. Junction Temperature** 



**Source Drain Diode Forward Voltage** 



**Threshold Voltage** 

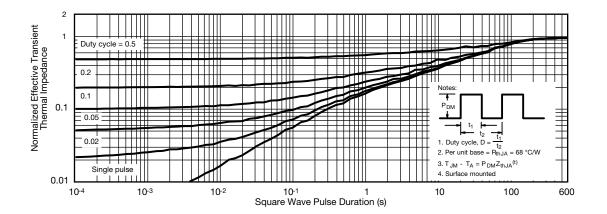


Safe Operating Area

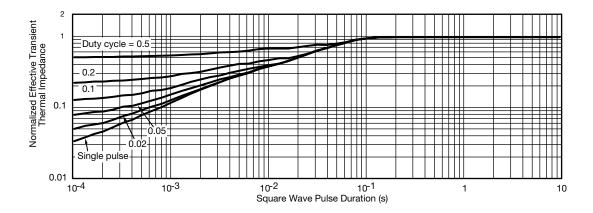
For technical questions, contact: automostech



### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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# PowerPAK® SO-8L Case Outline 2



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DIM		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN. NOM.		MAX.	
Α	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
E3	6.05	6.22	6.40	0.238	0.245	0.252	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W		0.23			0.009		
W1		0.41			0.016		
W2		2.82			0.111		
W3		2.96			0.117		
θ	0°	-	10°	0°	-	10°	

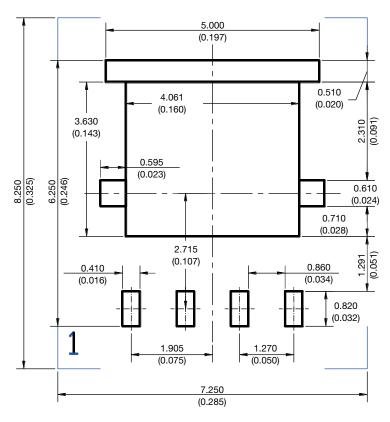
DWG: 6044

#### Note

• Millimeters will govern



#### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



## **Legal Disclaimer Notice**

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